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Fig. S1 plots relative energies as a function of $\sigma_F$ for independent vacancies (upper panel) and interstitials (lower panel) at all possible $x$-positions in the simulation cell with fully relaxed geometries.

FIG. S1: Defect formation energies for single vacancies and interstitials as a function of $x$ for $\sigma_F = 0.04, 0.05, 0.06, 0.07$. 

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